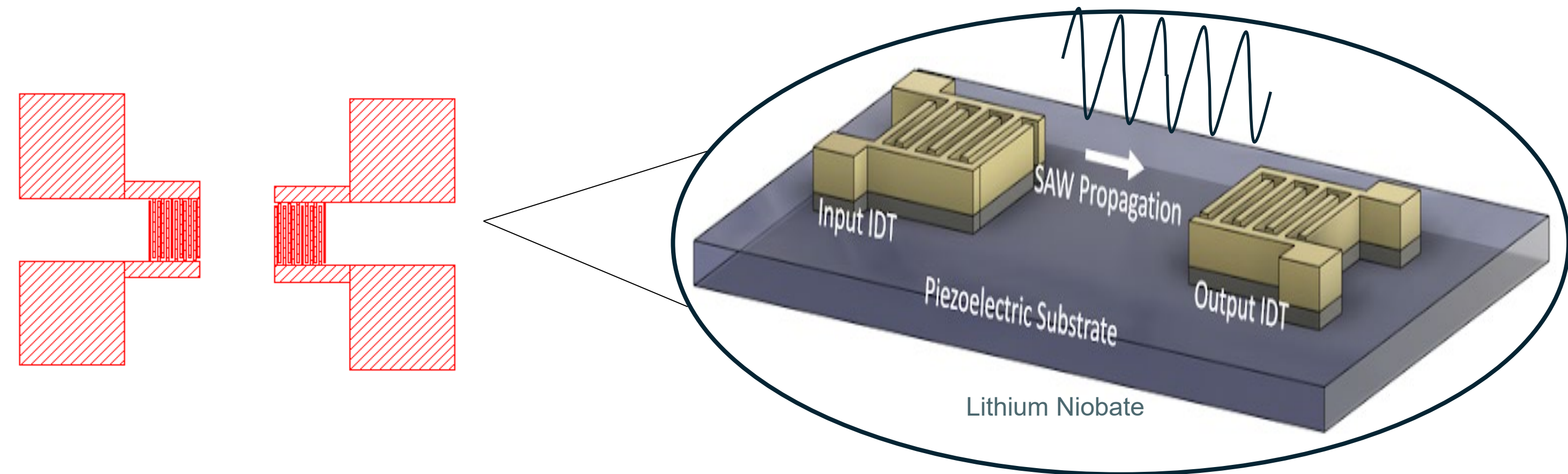
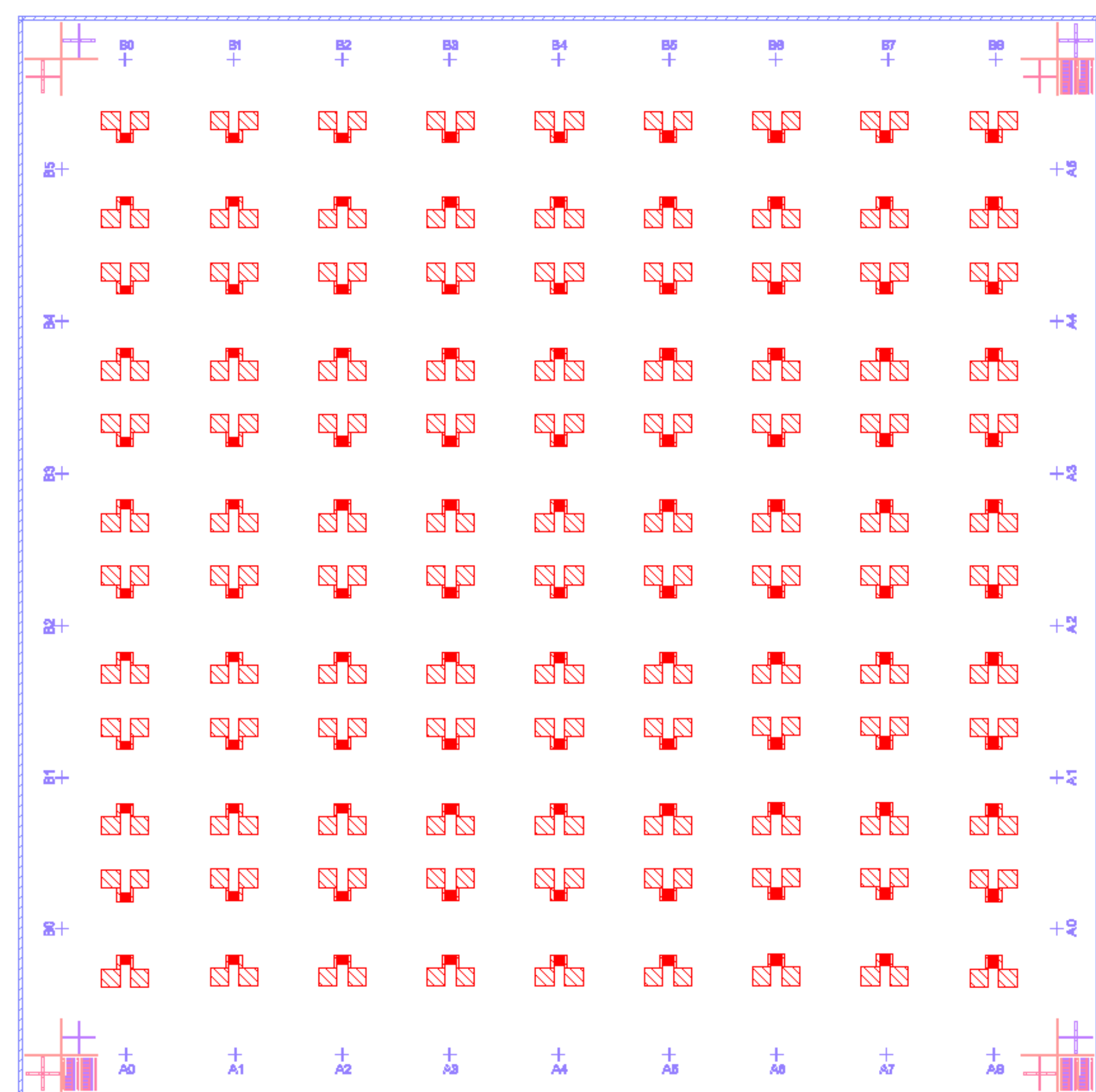


## Executive Summary



We developed a streamlined fabrication process using maskless laser lithography, optimized photoresist coating, and e-beam metal lift-off—achieving 16–24  $\mu\text{m}$  feature sizes on 128° Y-cut lithium niobate substrates with over 95% yield. This resulted in high throughput devices operate at 166–248 MHz with 99% electromechanical coupling efficiency. This approach meets current radio frequency (RF) filtering and sensing demands while enabling future scaling to GHz frequencies and straightforward integration of phase-change material (PCM) onto laser-ablated chip regions.

## Chip Design



Feature Size( $\mu\text{m}$ )	16	17	18	19	20	21	22	23	24
$f$ (MHz)	248	234	221	209	199	189	180	173	166

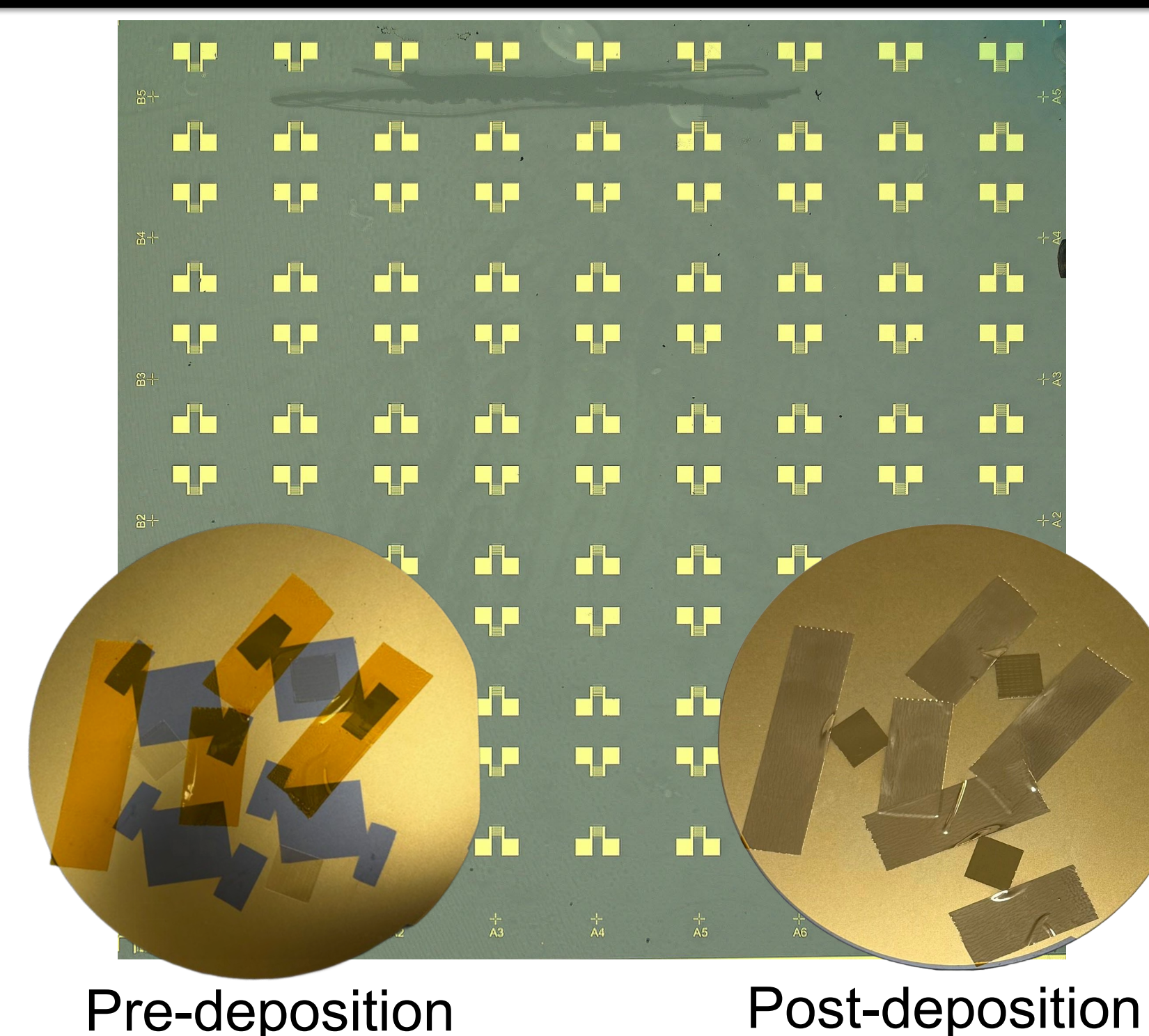
## Maskless Lithography Apparatus (MLA)

### MLA Tool



- Substrates undergo typical processes e.g., cleaned, spin-coated with photoresist, soft baked, exposed with the MLA, post-exposure baked, then developed.
- The MLA enabled direct, high-precision interdigitated transducers (IDT) patterning necessary for our devices without photomasks allowing for quick turn around time.
- Offers unparalleled flexibility to tweak electrode geometries between runs, fine-tuning filter bandwidths and resonance sharpness without reordering masks.

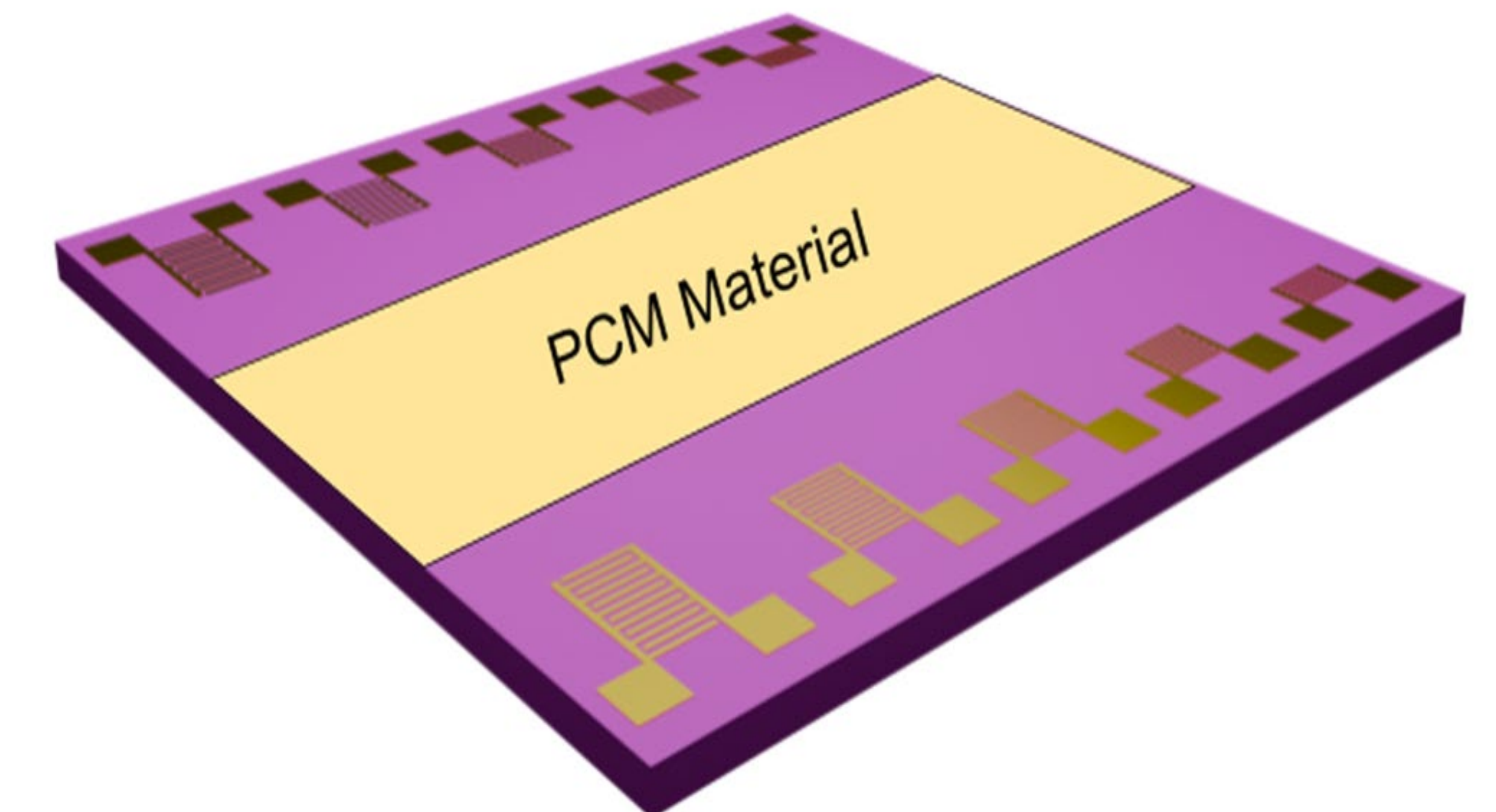
## Temescal E-beam Evaporator



- Metal deposition allows for high-purity, contamination-free metal films, making it ideal for applications where electrical performance and surface integrity are critical.
- 10 nm of titanium and 50 nm of gold are deposited on the first set of chips

## Future Device Design

### PCM Deposition



- The MLA is utilized to create trenches in a layer of photoresist to assist PCM deposition and alleviate potential fabrication difficulties from etching piezoelectric crystals.
- The combination of these techniques can be utilized to ease fabrication difficulties and promote reconfigurable/unidirectional devices.

## Conclusion

- Achieved SAW fabrication through a streamlined workflow delivering over 95 % yield with minimal process complexity and enabling rapid prototyping and scalable production.
- Characterization displayed operation across a 166–248 MHz band with a coupling efficiency of 99%, confirming robust device performance.
- Future improvements will focus on decreasing the wavelengths along with the deposition of PCM.

## Acknowledgement

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